Monday Morning, October 22, 2018

Advanced Surface Engineering Division Room 202C - Session SE+NS+TF-MoM

Nanostructured Thin Films and Coatings

Moderators: Jianliang Lin, Southwest Research Institute, Matjaz Panjan, Jozef Stefan Institute, Slovenia

8:20am SE+NS+TF-MoM1 The Role of Mechanical and Chemical Bonding Mechanisms in Adhesion of Nanoporous Anodic Aluminium Oxides (AAO), *Shoshan Abrahami*, Vrije Universiteit Brussel (VUB), Belgium; V.C. Gudla, Technical University of Denmark; K. Marcoen, Vrije Universiteit Brussel, Belgium; J.M.M. de Kok, Fokker Aerostructres; T. Hauffman, Vrije Universiteit Brussel, Belgium; R. Ambat, Technical University of Denmark; J.M.C. Mol, Technical University Delft, Netherlands; H. Terryn, Vrije Universiteit Brussel, Belgium

Anodic aluminum oxides (AAOs) are important nanostructures in many engineering applications. But despite their popular use, the important parameters that control their (dis-)bonding to an organic coating are not fully understood. This study uses an original approach that employs porous- and barrier AAO specimens for both chemical characterization and mechanical tests, thereby enabling the distinction between chemical and morphological contributions to the surface affinity for interfacial bonding. A validation for the cooperative effect of mechanical and chemical bonding mechanisms is given in this study. This was achieved by post-anodizing immersion of AAO's in sodium fluoride solution after anodizing in sulfuric acid (SAA) or a mixture of phosphoric- and sulfuric acid (PSA). Transmission electron microscopy (TEM) cross-section images show that fluorideassisted dissolution smoothed the oxide surface, removing the fibril-like top nanostructure of the porous oxides, which are important for dry adhesion. However, chemical surface modifications were dependent on the initial oxide composition, as measured by X-ray photoelectron spectroscopy (XPS) and Time-of-Flight Secondary Ion Mass Spectrometry (ToF-SIMS). Chemical analysis reveals that the surface hydroxyls of AAO are partially replaced by fluorides that do not form interfacial bonding with the epoxy resin. As a result, the peel strength of SAA under wet conditions is severely reduced due to these chemical changes. Conversely, fluorideassisted dissolution of surface phosphates in PSA compensates for the adsorbed fluorides and the wet peel strength of PSA panels is not further deteriorated.

[1] S.T. Abrahami et al., J. Phys. Chem. C, 119, 19967-19975 (2015).

[2] S.T. Abrahami et al., npj Materials Degradation, 1, 8 (2017).

[3] S.T. Abrahami et al., J. Phys. Chem. C, 120, 19670-19677 (2016).

9:00am SE+NS+TF-MoM3 Two-dimensional Hexagonal Boron Nitride (hBN) Layer Promoted Growth of Highly-oriented, Trigonal-structured Ta₂C(0001) Thin Films via Ultra-high Vacuum Sputter-deposition on Al₂O₃(0001), Koichi Tanaka, P. Arias, M.E. Liao, Y. Wang, H. Zaid, A. Aleman, M.S. Goorsky, S. Kodambaka, University of California, Los Angeles It is generally believed that single-crystalline substrates with either the bulk or surface structure and lattice constant identical or similar to that of the film being deposited are required for the growth of high-quality crystalline thin films. Recent studies have shown that deposition on van der Waals (vdW) layers can lead to highly-oriented thin films of a variety of crystal structures and lattice parameters. Here, we show that two-dimensional (2D) hexagonal boron nitride (hBN) layers (a = 0.250 nm and c = 0.667 nm) improve the crystallinity of trigonal-structured Ta₂C (a = 0.310 nm and c =0.494 nm) thin films sputter-deposited on $Al_2O_3(0001)$ substrates. Ta_2C layers of desired thickness ($t = 17 \sim 75$ nm) are grown on bare and hBNcovered Al₂O₃(0001) substrates via ultra-high vacuum direct current magnetron sputtering of TaC compound target in 20 mTorr pure Ar gas atmospheres at 1327 K. hBN layers are deposited via pyrolytic cracking of borazine (~600 L) onto Al₂O₃(0001) substrates at 1327 K. The as-deposited Ta₂C films are characterized in situ using Auger electron spectroscopy and low-energy electron diffraction and ex situ using X-ray diffraction (XRD) and transmission electron microscopy (TEM) based techniques. ω -2 θ XRD scans acquired from both Ta2C/Al2O3(0001) and Ta2C/hBN/Al2O3(0001) films with t = 17 nm exhibit only Ta₂C 0002*n* reflections (corresponding to c = 0.494nm) while thicker layers (t = 75 nm) reveal the presence of additional 10 1 reflections. However, the 0002 reflection peak intensities are 5.4-fold stronger for the Ta₂C layers on hBN/Al₂O₃(0001) than bare Al₂O₃(0001). High-resolution TEM images and associated Fourier transforms indicate that the layers are single-crystalline. XRD ϕ scans show six 60°-rotated 10 -1 2 peaks of Ta₂C at the same ϕ angles for 1 1 -2 6 of Al₂O₃ based on which we determine the epitaxial crystallographic relationships between the film and the substrate as Ta₂C(0002) || Al₂O₃(0006) with in-plane orientation of Ta₂C[1 0 -1 0] || Al₂O₃[1 1 -2 0]. We further show that 0002-oriented Ta₂C thicker films can be obtained by inserting hBN layers at regular intervals during the deposition of thicker Ta₂C films.

9:20am SE+NS+TF-MOM4 Nitride High Entropy Alloy Thin Films Deposited by Magnetron Sputtering and Cathodic Arc on Polymer Substrates: Structure and Electro-Mechanical Properties, *Ao Xia*, Montanuniversität Leoben, Austria; *R. Dedoncker*, Ghent University, Belgium; *M.J. Cordill*, Erich Schmid Institute of Materials Science, Austria; *D.J.M.G. Depla*, Ghent University, Belgium; *R. Franz*, Montanuniversität Leoben, Austria

In recent years a new class of materials has emerged in the field of metallurgy: high entropy alloys (HEAs). These metallic alloys consist of 5 to 13 metallic elements in an approximately equimolar ratio. Studies conducted on HEA bulk materials revealed promising combinations of properties, such as strength, ductility, corrosion resistance, wear resistance, hardness, diffusion and thermal conductivity. While research on bulk high entropy alloys has seen quite a boost over the past years, investigations on thin films are still a relatively unexplored area.

The focus of this report lies on the synthesis of MoNbTaVW HEA thin films by two different physical vapor deposition techniques, magnetron sputtering and cathodic arc deposition. The films were synthesized in Ar/N2 atmosphere with varying gas flows in order to study the influence of N addition on structure and properties of the HEA thin films. Analysis by X-ray diffraction revealed a phase change from body-centered cubic (bcc) in case of the metallic HEA films to face-centered cubic (fcc) for the nitrides. A slightly lower N2 gas flow is necessary in the case of magnetron sputter deposition to trigger the phase change than in the case of cathodic arc deposition. However, in both cases an increase in hardness was observed. For example, in the case of the films deposited by cathodic arc, the hardness increased from 18 to 30 GPa with the change from bcc to fcc phase. To further characterize the mechanical and electrical properties, the films were deposited on polymer substrates. The adhesion energy as determined from the geometry of buckles formed on the surface due to compressive stresses was a few J/m². In-situ uniaxial tensile tests revealed a brittle behavior of all films with crack onset strains of up to 3 %. The formation of elongated through thickness cracks caused a rather abrupt increase of the resistivity upon the crack appearance.

9:40am SE+NS+TF-MoM5 Isomeric Phase Composition and Mechanical Properties of NbN Nanocomposite Coatings Deposited by Modulated Pulsed Power Magnetron Sputtering, *Y.G. Li*, *H. Yuan, Z.T. Jiang, N. Pan, M.K. Lei*, Dalian University of Technology, China

Isomeric NbN nanocomposite coatings on stainless steel substrate with face-centered cubic phase δ -NbN and hexagonal phase δ' -NbN were deposited by modulated pulsed power magnetron sputtering under nitrogen flow rate f_{N2} from 15% to 30%. It was found that the nitrogen flow rate f_{N2} had a significant influence on the energy delivered in each macropulse, which led to a marked change in the phase composition and mechanical properties. The peak power decreases from 54 kW to 16 kW as $f_{\rm N2}$ increases from 15% to 30% with the energy delivered in each macropulse from 23.2 J to 9.8 J. When f_{N2} is at 15%, NbN coatings are mainly composed of δ' -NbN phase which usually exists at high f_{N2} or under high compressive residual stress showing (100) and (102) preferred orientation, while $\delta\text{-NbN}$ gradually appears with the preferred orientation from (111) to (200) as f_{N2} increases accompanied with the decrease of δ' -NbN phase composition. The hardness and modulus of isomeric NbN nanocomposite coatings go up to 36 GPa from 30 GPa and 460 GPa from 366 GPa as f_{N2} increases to 20% with residual compressive stress from 0.47 GPa to 1.93 GPa, then decrease to 29 GPa and 389 GPa with residual compressive stress of 1.01 GPa showing a nonlinear response with peak power. The NbN nanocomposite coatings with more δ' -NbN phase show higher hardness and better toughness due to the composition variation of $\delta'\text{-NbN}$ and $\delta\text{-NbN}$ phases. The phase composition from $\delta'\text{-NbN}$ to $\delta\text{-NbN}$ phase should attribute to the delivered energy difference by peak power, and the anomalous increase in hardness should be originated from strengthening of the nanocomposite structure.

10:00am SE+NS+TF-MoM6 Ab initio Guided Development of Ternary Borides: A Case Study of Ti-B-N, Ti-Zr-B, Ti-W-B, Ta-W-B, and V-W-B Systems, V. Moraes, R. Hahn, M. Bartosik, H. Riedl, TU Wien, Austria; H. Euchner, Ulm University, Austria; D. Holec, Montanuniversität Leoben, Austria; Paul Heinz Mayrhofer, TU Wien, Austria

Transition-metal borides are a special class of ultra-high temperature ceramics. Among these, refractory borides such as TiB₂, ZrB₂, VB₂, TaB₂, and

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WB₂ are attractive candidates for many applications – ranging from high temperature electrodes, cutting tools, and molten metal containment to microelectronic buffer layers – because of their thermomechanical and chemical properties, their high melting temperatures up to ~3500 °C, and excellent high temperature strengths. However, these diborides have a comparably low fracture toughness of K_{IC} ~1 MPaVm (here, basically obtained by in-situ micromechanical cantilever bending tests).

How diboride materials can be designed - implementing quantum chemistry guided materials design concepts - to allow for a combination of high strength, ductility, and thermal stability, is the focus of this talk. We will use recent developments of diborides - where we applied alloying and architecture concepts (e.g., composition and/or phase modulated layers) to explore such materials-science-based guidelines for improved properties. Especially the phase stability (with respect to chemistry and temperature) of diborides is an extremely interesting task. For example, only WB₂ (among all binary diborides, except for TcB₂) provides a G/B ratio below 0.5 (~0.34) and a positive Cauchy pressure C13-C44 (~73 GPa), which are typical indications for dominating non-directional bonds and thus a more ductile behavior. But WB2provides these properties only in its metastable α -structure (AlB₂-prototype) and not for its thermodynamically stable ω -structure (WB₂-prototype). With the help of ternary diborides, such as $(Ti,W)B_2$ or even $(Ta,W)B_2$, the α -structure can be stabilized (even up to ~1200 °C). Even more important is a selective sensitivity of the α - and the ω -structure for the formation of vacancies. Especially, when using physical vapor deposition (PVD) techniques at moderate temperatures (here ~400 °C) the content of vacancies (and point defects in general) is rather high. Such defects are less penalized in the $\alpha\text{-}$ than in the $\omega\text{-}$ structure, allowing for growing even single-phased α -WB₂ by PVD, exhibiting hardnesses H of ~40 GPa combined with high fracture toughness of Kic ~3 MPaVm.

With the help of superlattices, nanocolumnar and nanocomposite structures, we show that also with architectural concepts, strength (H ~45 GPa) and ductility (K_{ic} ~3.5 MPaVm) can be improved simultaneously.

The individual concepts will allow designing materials to meet the evergrowing demand for further improved coatings, tailor made for specific applications.

10:40am SE+NS+TF-MoM8 Toughness Enhancement in Hard Ceramic Films by Alloy Design, Hanna Kindlund, Department of Mechanical and Aerospace Engineering, University of California Los Angeles (UCLA) INVITED Transition-metal nitrides are refractory ceramics with high hardness, excellent wear resistance, high temperature stability, and good chemical inertness. Therefore, they are attractive in many applications, especially, as protective coatings against scratches, erosion, corrosion, and wear.

Tremendous efforts have been dedicated in enhancing hardness of ceramic films. However, in addition to high hardness, most applications also require high ductility, to avoid brittle failure due to cracking when coatings are subjected to high thermo-mechanical stresses. However, transition-metal nitrides, as most ceramics, are usually brittle, exhibiting low ductility and hence poor toughness.

Enhancing toughness in ceramic films is a challenging task that requires a fundamental understanding of the mechanical behavior of materials, which depends on their microstructure, electronic structure, and bonding nature. Theoretical studies using *ab initio* calculations predicted that alloys of VN with WN or MoN exhibit enhanced toughness as a result of their high valence electron concentrations, leading to an orbital overlap which favors ductility during shearing.

Here, I present experimental results on the growth of $V_{1 \star} W_x N_V$ and $V_{1 \star} M_0 x N_V$ alloy thin films, their microstructure, mechanical properties and electronic structure, and relate these properties with their enhanced ductility, demonstrating that it is possible to develop hard-yet-ductile ceramic coatings.

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